

Erratum

High-Mobility Hydrogenated Fluorine-Doped Indium Oxide Film for Passivating Contacts c-Si Solar Cells (ACS Appl. Mater. Interfaces (2019) 11:49 (45586–45595) DOI: 10.1021/acsami.9b14709)

Han, Can; Mazzarella, Luana; Zhao, Yifeng; Yang, Guangtao; Procel, Paul; Tijssen, Martijn; Montes, Ana; Isabella, Olindo; Zeman, Miro; More Authors

DOI

[10.1021/acsami.1c02993](https://doi.org/10.1021/acsami.1c02993)

Publication date

2021

Document Version

Final published version

Published in

ACS Applied Materials and Interfaces

Citation (APA)

Han, C., Mazzarella, L., Zhao, Y., Yang, G., Procel, P., Tijssen, M., Montes, A., Isabella, O., Zeman, M., & More Authors (2021). Erratum: High-Mobility Hydrogenated Fluorine-Doped Indium Oxide Film for Passivating Contacts c-Si Solar Cells (ACS Appl. Mater. Interfaces (2019) 11:49 (45586–45595) DOI: 10.1021/acsami.9b14709). *ACS Applied Materials and Interfaces*, 13(10), 12636. <https://doi.org/10.1021/acsami.1c02993>

Important note

To cite this publication, please use the final published version (if applicable).
Please check the document version above.

Copyright

Other than for strictly personal use, it is not permitted to download, forward or distribute the text or part of it, without the consent of the author(s) and/or copyright holder(s), unless the work is under an open content license such as Creative Commons.

Takedown policy

Please contact us and provide details if you believe this document breaches copyrights.
We will remove access to the work immediately and investigate your claim.

Correction to “High-Mobility Hydrogenated Fluorine-Doped Indium Oxide Film for Passivating Contacts c-Si Solar Cells”

Can Han,* Luana Mazzarella, Yifeng Zhao, Guangtao Yang, Paul Procel, Martijn Tijssen, Ana Montes, Luca Spitaleri, Antonino Gulino, Xiaodan Zhang, Olindo Isabella,* and Miro Zeman

ACS Appl. Mater. Interfaces 2019, 11, 49, 45586–45595. DOI: 10.1021/acsami.9b14709



Cite This: ACS Appl. Mater. Interfaces 2021, 13, 12636–12636



Read Online

ACCESS |

Metrics & More

Article Recommendations

The authors inadvertently misreported the order of magnitude of the TCO deposition pressure, for which all “ 10^{-3} Pa” should be intended as “Pa”. The authors regret for the mistake. These errors do not affect the conclusions of the work.

The following errors needs to be corrected in the article.

Page 45587. EXPERIMENTAL SECTION, 2.1.

“ 2.50×10^{-3} Pa” and “ 2.20×10^{-3} Pa” should be “2.50 Pa” and “2.20 Pa”, respectively.

Page 45588. RESULTS AND DISCUSSION, 3.1.

All the “ $\dots \times 10^{-5}$ Pa” should be “ $\dots \times 10^{-2}$ Pa”.

The physical unit of the “ 10^{-5} Pa” in the x-axis of Figure 2 should also be “ 10^{-2} Pa”. The correct Figure 2 appears below:

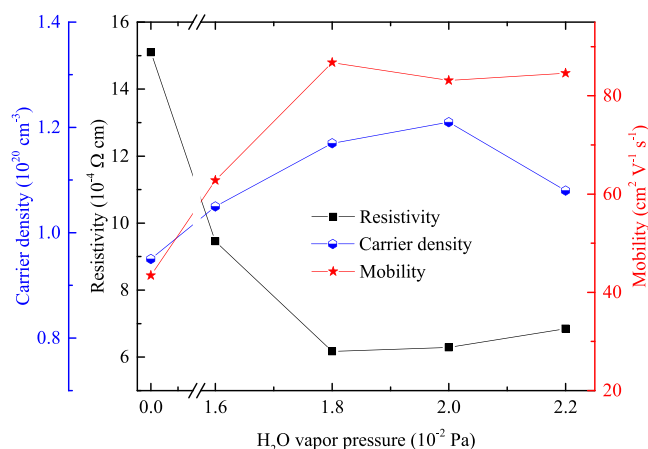


Figure 2. Resistivity (ρ), carrier density (N_c), and Hall mobility (μ_e) of as-grown In_2O_3 -based films as a function of variable H_2O vapor pressure.

Published: March 4, 2021

